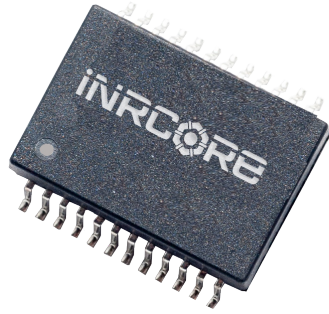


10G BASE-T PoE (++) TRANSFORMER MODULE



Ruggedized



- Compliant with IEEE 802.3ab for 1000 Base-T
- 120µH OCL with 27mA DC bias, at 100KHz 100mV
- Current Rating: 900mA Max per pair
- Storage Temperature: -55°C to +125°C
- Operating Temperature:
 - 10GB-6013: -40°C to +85°C
 - 10GB-6013X: -55°C to +125°C
- Terminal Finish: Sn/Pb (Pure tin for RoHS version)
- Moisture Sensitivity Level: 3

Electrical Specifications @ 25°C

Part Number	Insertion Loss (dB MAX)			Return Loss (dB MIN)					Crosstalk (dB MIN)				DM to CM Rejection (dB MIN)			DWV @5s (Vrms MIN)
	100 KHz	1-300 MHz	400-500 MHz	1 MHz	100 MHz	300 MHz	400 MHz	500 MHz	1 MHz	100 MHz	400 MHz	500 MHz	1 MHz	250 MHz	500 MHz	
10GB-6013	3	1.20	3	22	18	12	10	8	40	37	30	25	40	30	22	1500
10GB-6013X	3	1.20	3	22	18	12	10	8	40	37	30	25	40	30	22	1500

NOTES:

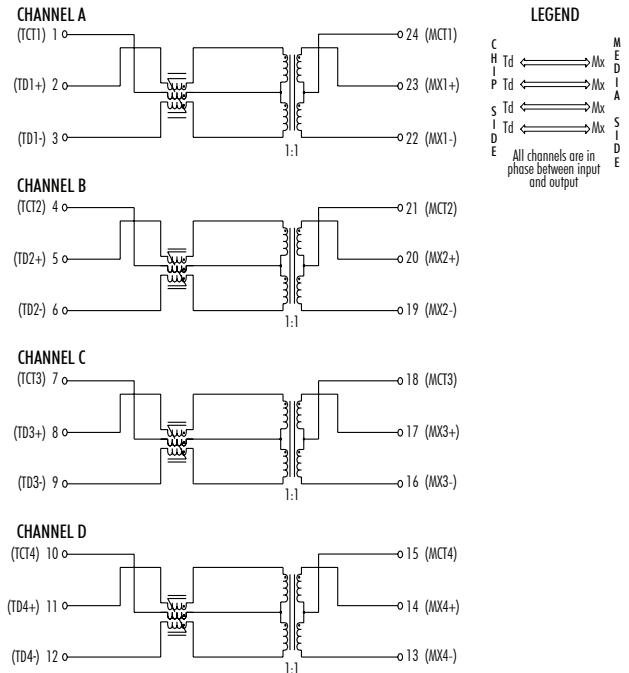
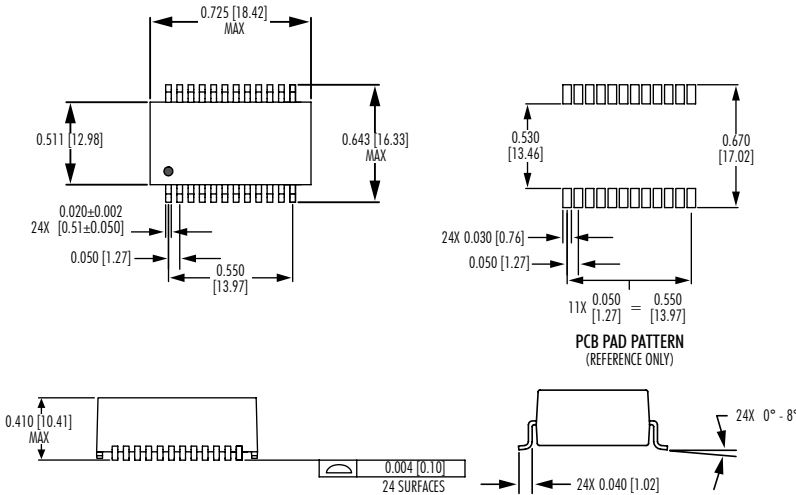
- Add suffix "NL" for RoHS compliant version; i.e. 10GB-6013 becomes 10GB-6013NL. NL parts have 100% SN Lead Finish (MSL:4)
- For Tape & Reel packaging, add "T" suffix at the end of the part number: i.e. 10GB-6013NLT.

Mechanicals

Electrical Schematics

10GB-6013 / 10GB-6013X

Dimensions: inch [mm]
Tolerance (unless otherwise specified): ±0.010 [0.25]



10G BASE-T PoE (++) TRANSFORMER MODULE

Ruggedized



Tin/Lead Recommended Reflow Profile (Based on J-STD-020D)



T_{SMIN} (°C)	T_{SMAX} (°C)	T_L (°C)	T_P (°C MAX)	t_s (s)	t_L (s)	t_p (s MAX)	Ramp-up rate (T_L to T_p)	Ramp-down rate (T_p to T_L)	Time 25°C to peak temperature (s MAX)
100	150	183	235	60 - 120	60 - 150	20	3°C/s MAX	6°C/s MAX	360

NOTES:

1. All temperatures measured on the package leads.
2. Maximum times of reflow cycle: 2

